

IN THE CLAIMS:

Please amend claims 1 through 4 and 6 as follows:

1. (Amended) A semiconductor device comprising:

a semiconductor substrate;

[at least an] a first portion comprising a plurality of active [region] regions formed in the semiconductor substrate;

a plurality of isolation regions[for] separating the active regions from each other;

a second section comprising at least one trench having an interior surface;

a surface insulating film formed on a surface of the active regions [region of the semiconductor substrate] in the first portion and on the interior surface of said at least one trench in the second portion; and

a conductive film formed on the surface insulating film, wherein the surface insulating film is [formed relatively] sufficiently thin to [work] function as an electric fuse.

2. (Amended) The semiconductor device according to claim 1, further comprising:

a plurality of surface insulating films, having different thicknesses, formed on a surface of the active regions in the first portion and on the interior surface of said at least one trench in the second portion [region of the semiconductor substrate; said surface insulating films being formed in a different thickness each other]; and

a plurality of conductive films formed on each of the surface insulating films in the first portion;

wherein one of the surface insulating films has a [having] smaller thickness than the other insulating films and is the insulating film which is formed on the interior surface of said at least one trench in the second portion and is capable of functioning [is used] as an electric fuse.

3. (Amended) [A] The semiconductor device [comprising:
a semiconductor substrate;
at least a trench formed in the semiconductor substrate;
a surface insulating film formed along a surface of the trench of the
semiconductor substrate; and
a conductive film formed on the surface insulating film] according to claim 1,
wherein:

the plurality of insulating films are gate oxide films; and
the plurality of conductive films are gate electrodes.

4. (Amended) A semiconductor device comprising:
a semiconductor substrate;
at least a trench formed in the semiconductor substrate;
a surface insulating film formed along a surface of the trench of the
semiconductor substrate; and
a conductive film formed on the surface insulating film; [The semiconductor
device according to claim 3,]